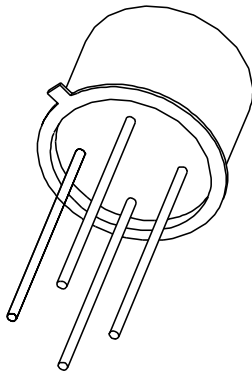


DATA SHEET



BRY39

Programmable unijunction
transistor/

Silicon controlled switch

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jul 24

Programmable unijunction transistor/ Silicon controlled switch

BRY39**FEATURES**

- Silicon controlled switch
- Programmable unijunction transistor.

APPLICATIONS

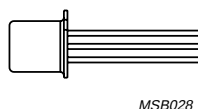
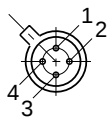
- Switching applications such as:
 - Motor control
 - Oscillators
 - Relay replacement
 - Timers
 - Pulse shapers, etc.

DESCRIPTION

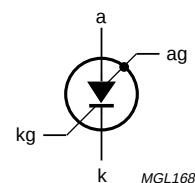
Silicon planar PNPN switch or trigger device in a TO-72 metal package. It is an integrated PNP/NPN transistor pair with all electrodes accessible.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode gate
3	anode gate (connected to case)
4	anode



MSB028



MGL168

Fig.1 Simplified outline (TO-72) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Silicon controlled switch				
PNP TRANSISTOR				
V_{EBO}	emitter-base voltage	open collector	-70	V
NPN TRANSISTOR				
V_{CBO}	collector-base voltage	open emitter	70	V
I_{ERM}	repetitive peak emitter current		-2.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	275	mW
T_j	junction temperature		150	°C
V_{AK}	forward on-state voltage	$I_A = 50\text{ mA}$; $I_{AG} = 0$; $R_{KG-K} = 10\text{ k}\Omega$	1.4	V
I_H	holding current	$I_{AG} = 10\text{ mA}$; $V_{BB} = -2\text{ V}$; $R_{KG-K} = 10\text{ k}\Omega$	1	mA
t_{on}	turn-on time		0.25	μs
t_{off}	turn-off time		15	μs
Programmable unijunction transistor				
V_{GA}	gate-anode voltage		70	V
I_A	anode current (DC)	$T_{amb} \leq 25\text{ °C}$	175	mA
T_j	junction temperature		150	°C
I_p	peak point current	$V_S = 10\text{ V}$; $R_G = 10\text{ k}\Omega$	0.2	μA

Programmable unijunction transistor/ Silicon controlled switch

BRY39

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ }^{\circ}\text{C}$	–	275	mW
T_{stg}	storage temperature		–65	+200	$^{\circ}\text{C}$
T_{j}	junction temperature		–	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^{\circ}\text{C}$
Silicon controlled switch					
V_{CBO}	collector-base voltage PNP NPN	open emitter	– –	–70 70	V V
V_{CER}	collector-emitter voltage PNP NPN	$R_{\text{BE}} = 10\text{ k}\Omega$	– –	– 70	V V
V_{CEO}	collector-emitter voltage PNP NPN	open base	– –	–70 –	V V
V_{EBO}	emitter-base voltage PNP NPN	open collector	– –	–70 5	V V
I_{C}	collector current (DC) PNP NPN	note 1	– –	– 175	mA
I_{CM}	peak collector current PNP NPN	note 2	– –	– 175	mA
I_{E}	emitter current (DC) PNP NPN		– –	175 –175	mA mA
I_{ERM}	repetitive peak emitter current PNP NPN	$t_{\text{p}} = 10\text{ }\mu\text{s}; \delta = 0.01$	– –	2.5 –2.5	A A
Programmable unijunction transistor					
V_{GA}	gate-anode voltage		–	70	V
I_{A}	anode current (AV)	$T_{\text{amb}} \leq 25\text{ }^{\circ}\text{C}$	–	175	mA

Programmable unijunction transistor/ Silicon controlled switch

BRY39

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{ARM}	repetitive peak anode current	$t_p = 10 \mu s$; $\delta = 0.01$	–	2.5	A
I_{ASM}	non-repetitive peak anode current	$t_p = 10 \mu s$; $T_j = 150 \text{ }^\circ\text{C}$	–	3	A
dl_A/dt	rate of rise of anode current	$I_A \leq 2.5 \text{ A}$	–	20	A/ μs

Notes

1. Provided the I_E rating is not exceeded.
2. During switching on, the device can withstand the discharge of a capacitor of a maximum value of 500 pF. This capacitor is charged when the transistor is in cut-off condition, with a collector supply voltage of 160 V and a series resistance of 100 k Ω .

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th j-a}$	thermal resistance from junction to ambient	in free air	450	K/W

CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Silicon controlled switch					
INDIVIDUAL PNP TRANSISTOR					
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = -70 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -70 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$	–	–10	μA
h_{FE}	DC current gain	$I_E = 1 \text{ mA}$; $V_{CE} = -5 \text{ V}$	3	15	
INDIVIDUAL NPN TRANSISTOR					
I_{CER}	collector cut-off current	$V_{CE} = 70 \text{ V}$; $R_{BE} = 10 \text{ k}\Omega$	–	100	nA
		$V_{CE} = 70 \text{ V}$; $R_{BE} = 10 \text{ k}\Omega$; $T_j = 150 \text{ }^\circ\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$	–	10	μA
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 1 \text{ mA}$	–	0.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 1 \text{ mA}$	–	0.9	V
h_{FE}	DC current gain	$I_C = 10 \text{ mA}$; $V_{CE} = 2 \text{ V}$	50	–	
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 20 \text{ V}$	–	5	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 1 \text{ V}$; $f = 1 \text{ MHz}$	–	25	pF
f_T	transition frequency	$I_C = 10 \text{ mA}$; $V_{CE} = 2 \text{ V}$; $f = 100 \text{ MHz}$	100	–	MHz
COMBINED DEVICE					
V_{AK}	forward on-state voltage	$R_{KG-K} = 10 \text{ k}\Omega$			
		$I_A = 50 \text{ mA}$; $I_{AG} = 0$	–	1.4	V
		$I_A = 50 \text{ mA}$; $I_{AG} = 0$; $T_j = -55 \text{ }^\circ\text{C}$	–	1.9	V
		$I_A = 1 \text{ mA}$; $I_{AG} = 10 \text{ mA}$	–	1.2	V
I_H	holding current	$V_{BB} = -2 \text{ V}$; $I_{AG} = 10 \text{ mA}$; $R_{KG-K} = 10 \text{ k}\Omega$; see Fig.14	–	1	mA

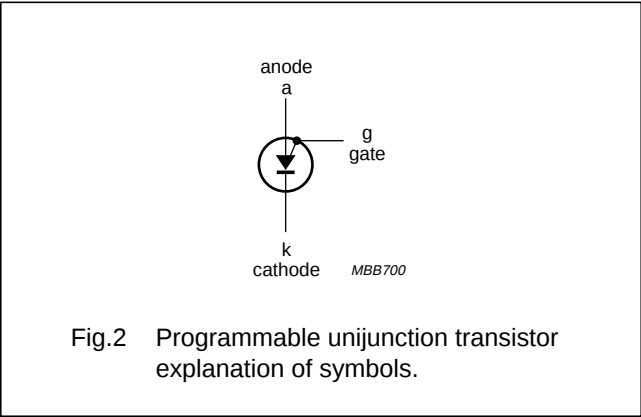
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Silicon controlled switch

BRY39

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
SWITCHING TIMES					
t _{on}	turn-on time	V _{KG-K} = -0.5 to 4.5 V; R _{KG-K} = 1 kΩ; see Figs 15 and 16	—	0.25	μs
		V _{KG-K} = -0.5 to 0.5 V; R _{KG-K} = 10 kΩ	—	1.5	μs
t _{off}	turn-off time	R _{KG-K} = 10 kΩ; see Figs 17 and 18	—	15	μs
Programmable unijunction transistor					
I _p	peak point current	V _S = 10 V; R _G = 10 kΩ; see Figs 3 and 8	—	0.2	μA
		V _S = 10 V; R _G = 100 kΩ; see Figs 3 and 8	—	0.06	μA
I _v	valley point current	V _S = 10 V; R _G = 10 kΩ; see Figs 3 and 8	—	2	μA
		V _S = 10 V; R _G = 100 kΩ; see Figs 3 and 8	—	1	μA
V _{offset}	offset voltage	typical curve; I _A = 0; for V _P and V _S see Fig.8	—	—	V
I _{GAO}	gate-anode leakage current	I _K = 0; V _{GA} = 70 V	—	10	nA
I _{GKS}	gate-cathode leakage current	V _{AK} = 0; V _{KG} = 70 V	—	100	nA
V _{AK}	anode-cathode voltage	I _A = 100 mA	—	1.4	V
V _{OM}	peak output voltage	V _{AA} = 20 V; C = 10 nF; see Figs 9 and 11	6	—	V
t _r	rise time	V _{AA} = 20 V; C = 10 nF; see Fig.11	—	80	ns

Explanation of symbols

For application of the BRY39 as a programmable unijunction transistor, only the anode gate is used. To simplify the symbols, the term gate instead of anode gate will be used (see Fig.2).



Programmable unijunction transistor/
Silicon controlled switch

BRY39

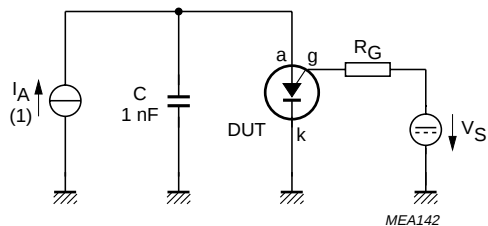


Fig.3 Programmable unijunction transistor test circuit for peak and valley points.

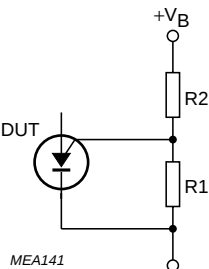


Fig.4 Programmable unijunction transistor with 'program' resistors R1 and R2.

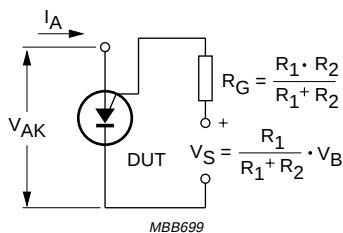


Fig.5 Programmable unijunction transistor equivalent test circuit for characteristics testing.

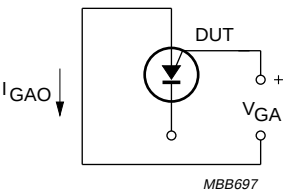


Fig.6 Programmable unijunction transistor equivalent test circuit for gate-anode leakage current.

Programmable unijunction transistor/
Silicon controlled switch

BRY39

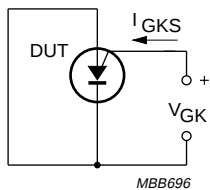


Fig.7 Programmable unijunction transistor equivalent test circuit for gate-cathode leakage current.

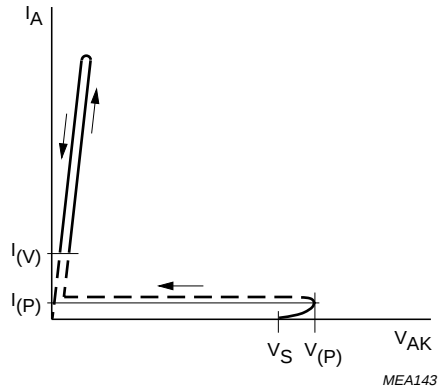


Fig.8 Programmable unijunction transistor offset voltage.

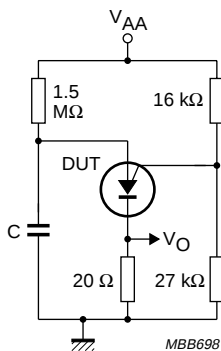


Fig.9 Programmable unijunction transistor test circuit for peak output voltage.

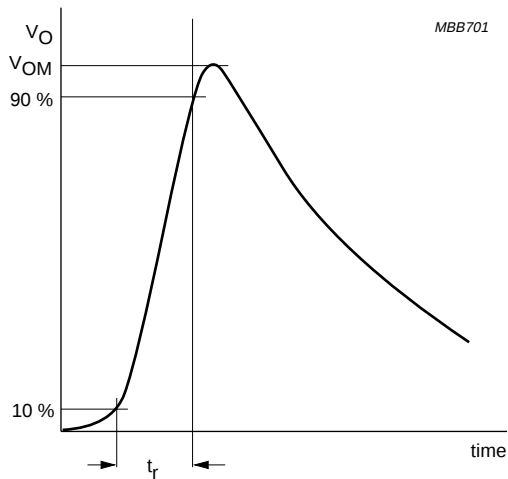
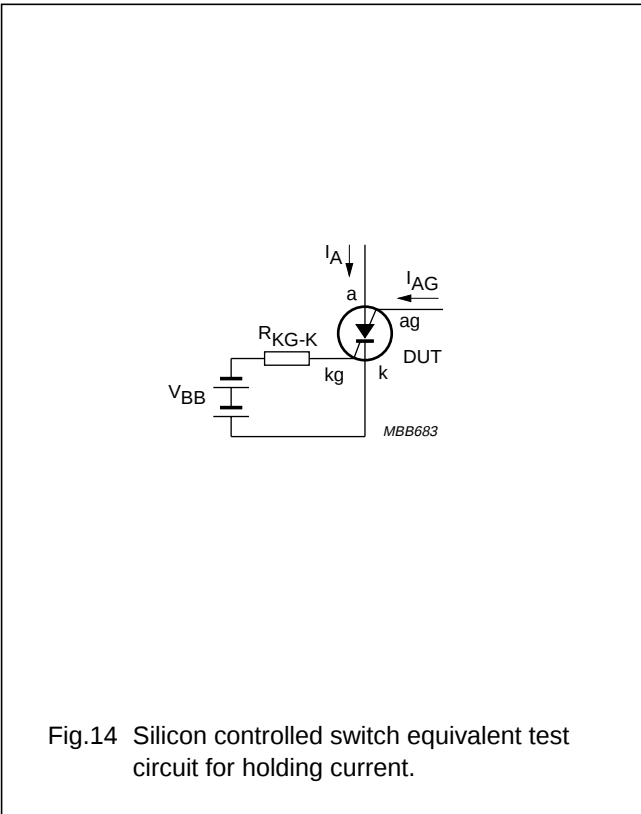
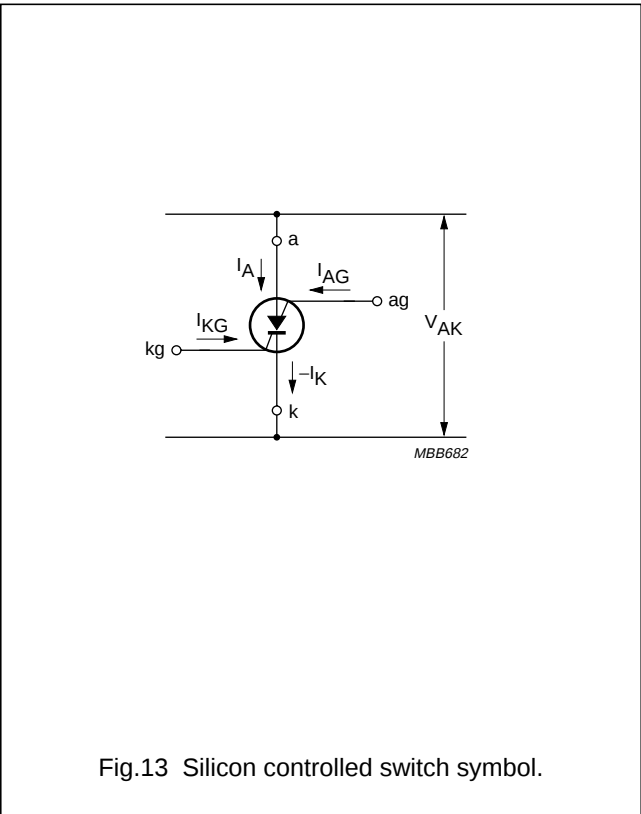
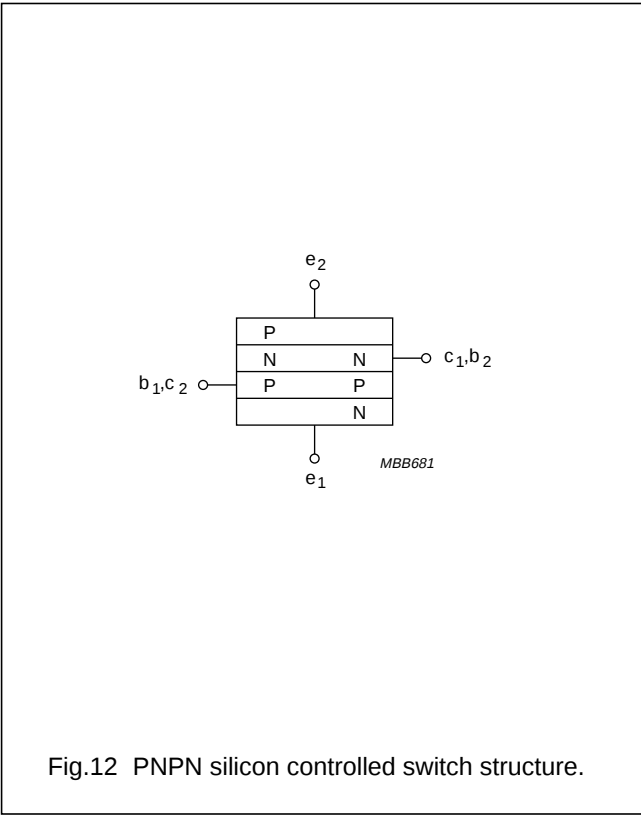
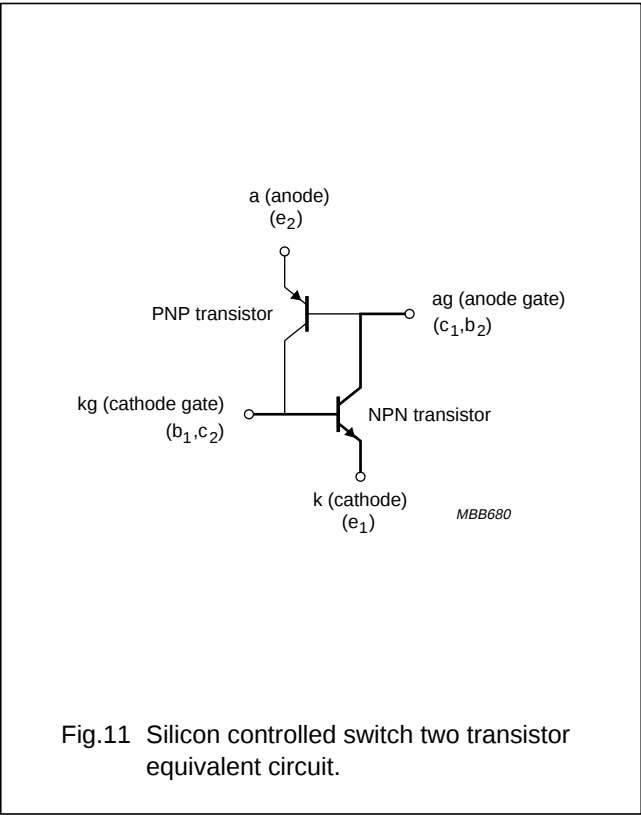


Fig.10 Programmable unijunction transistor peak output voltage.

Programmable unijunction transistor/
Silicon controlled switch

BRY39



Programmable unijunction transistor/
Silicon controlled switch

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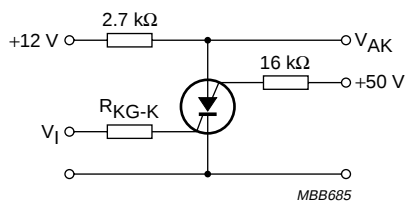


Fig.15 Silicon controlled switch test circuit for turn-on time.

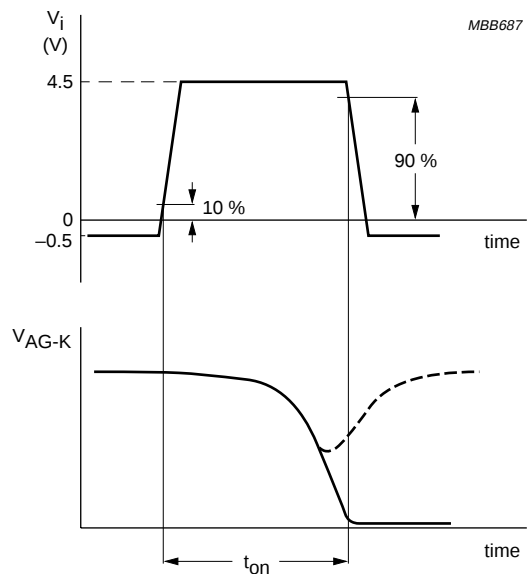


Fig.16 Silicon controlled switch pulse duration increased until dashed curve disappears.

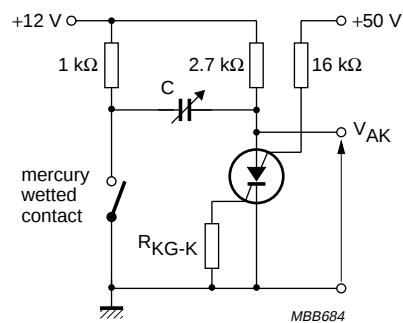


Fig.17 Silicon controlled switch test circuit for turn-on time.

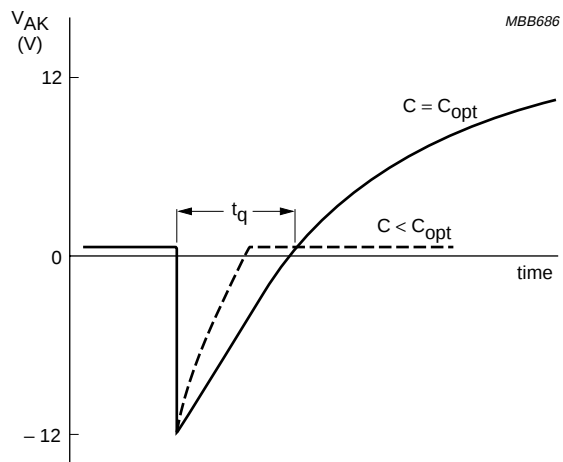
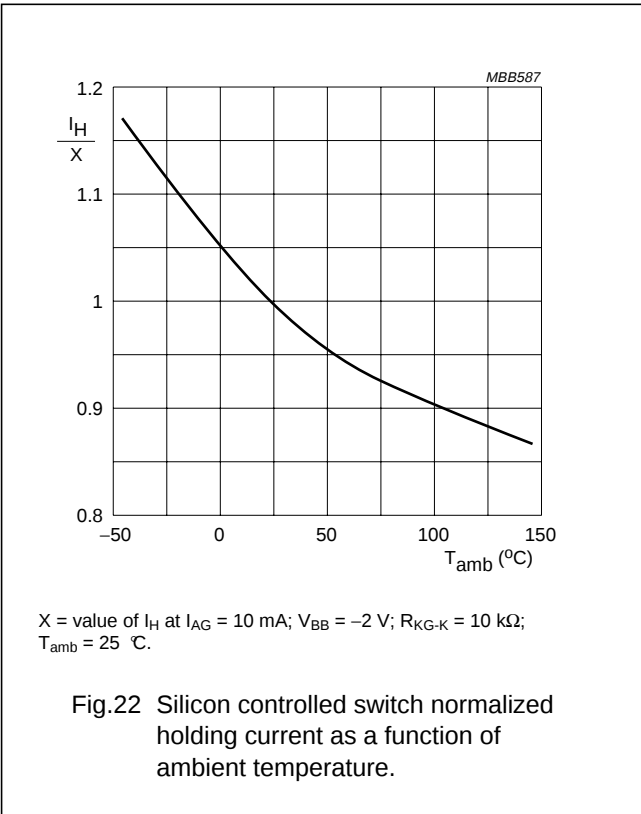
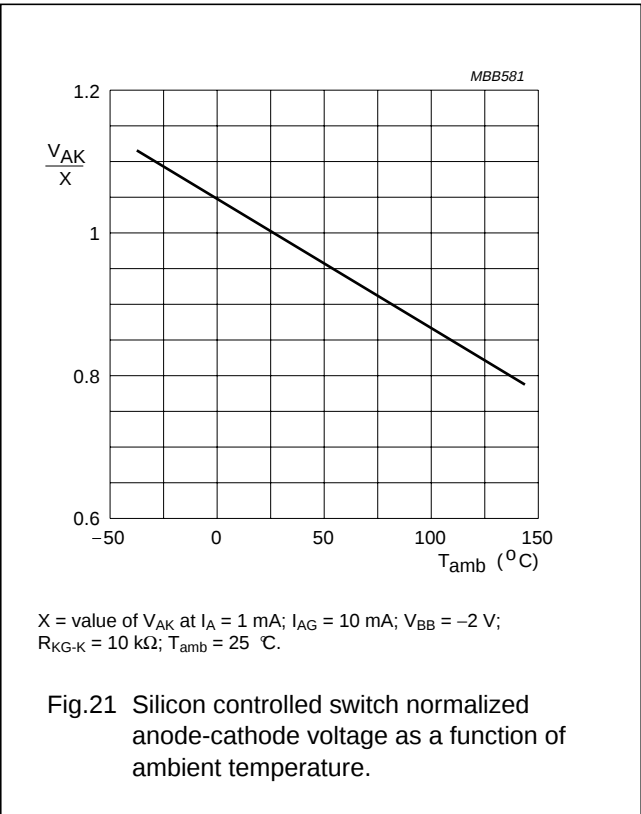
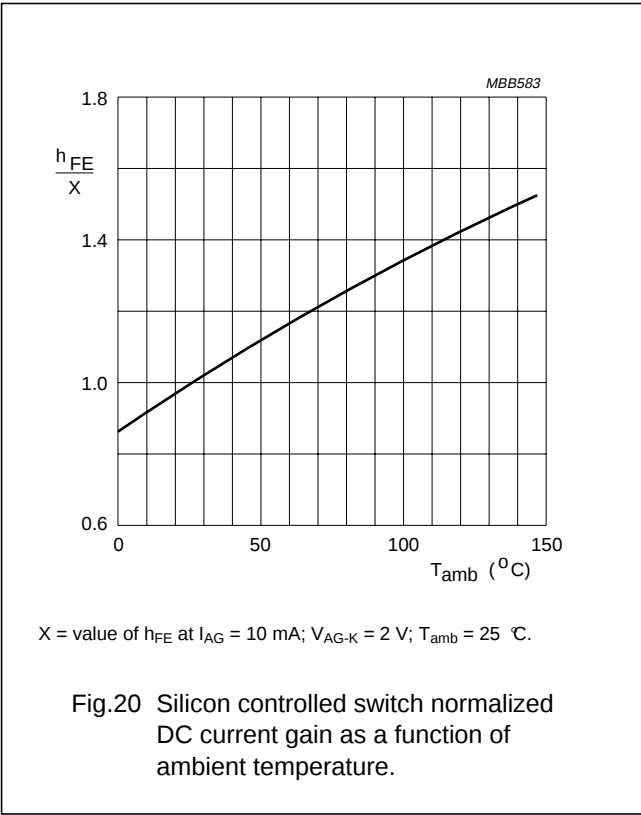
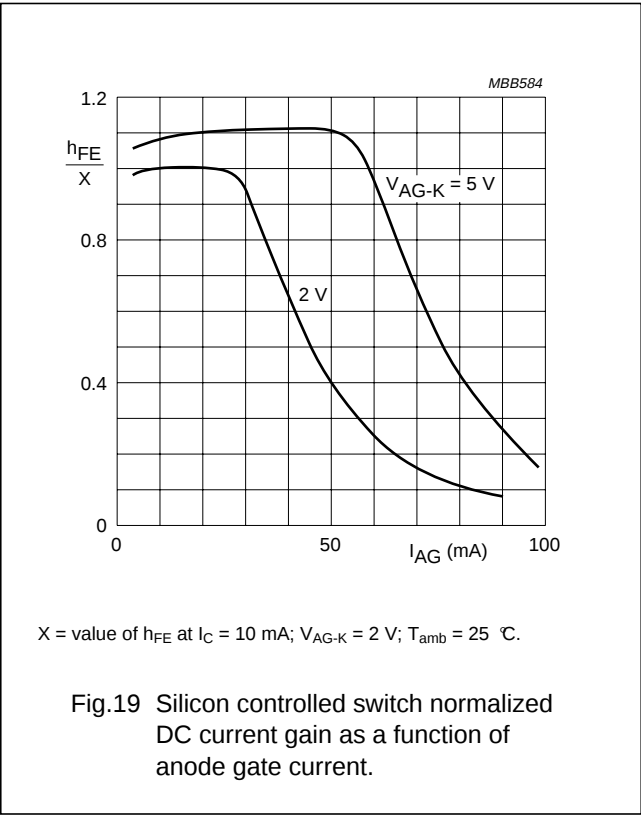


Fig.18 Silicon controlled switch capacitance increased until $C = C_{opt}$ dashed curve disappears.

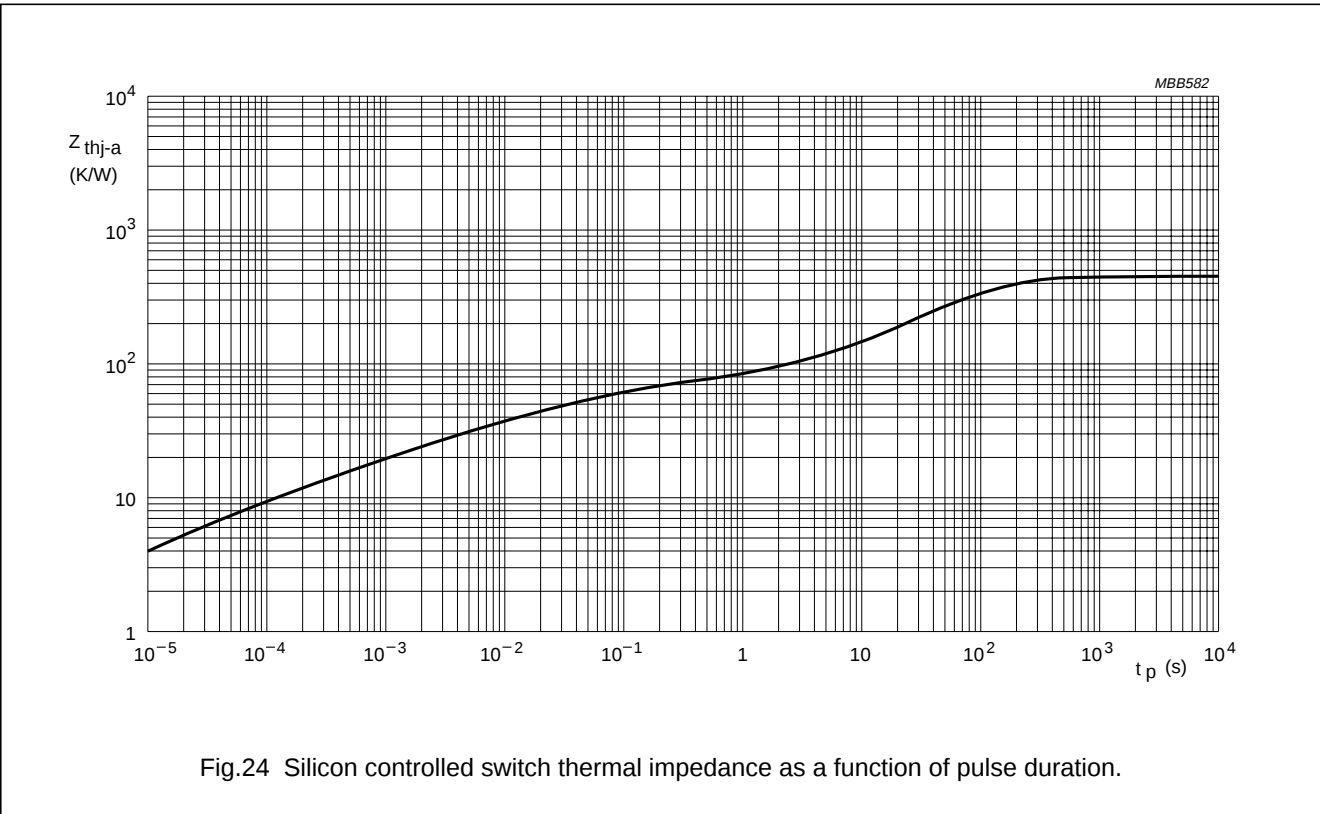
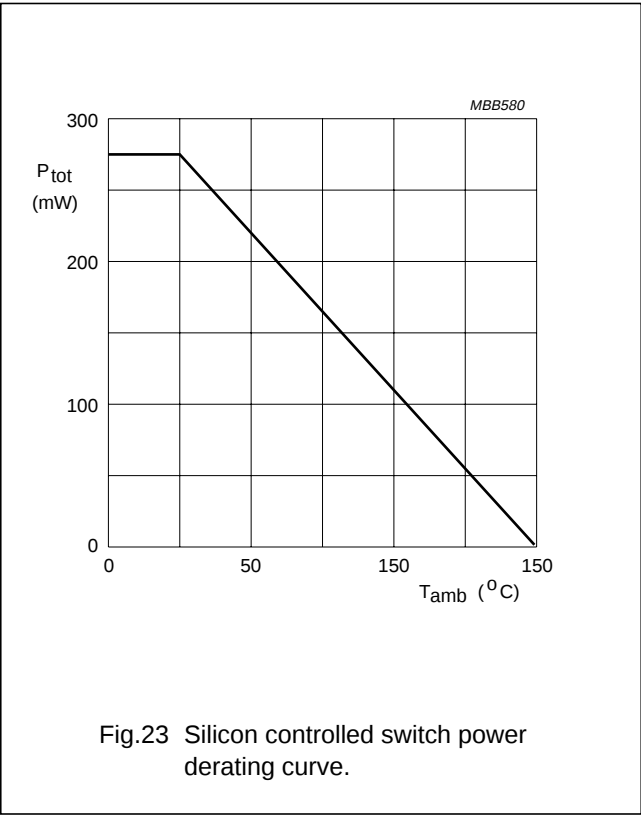
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Silicon controlled switch

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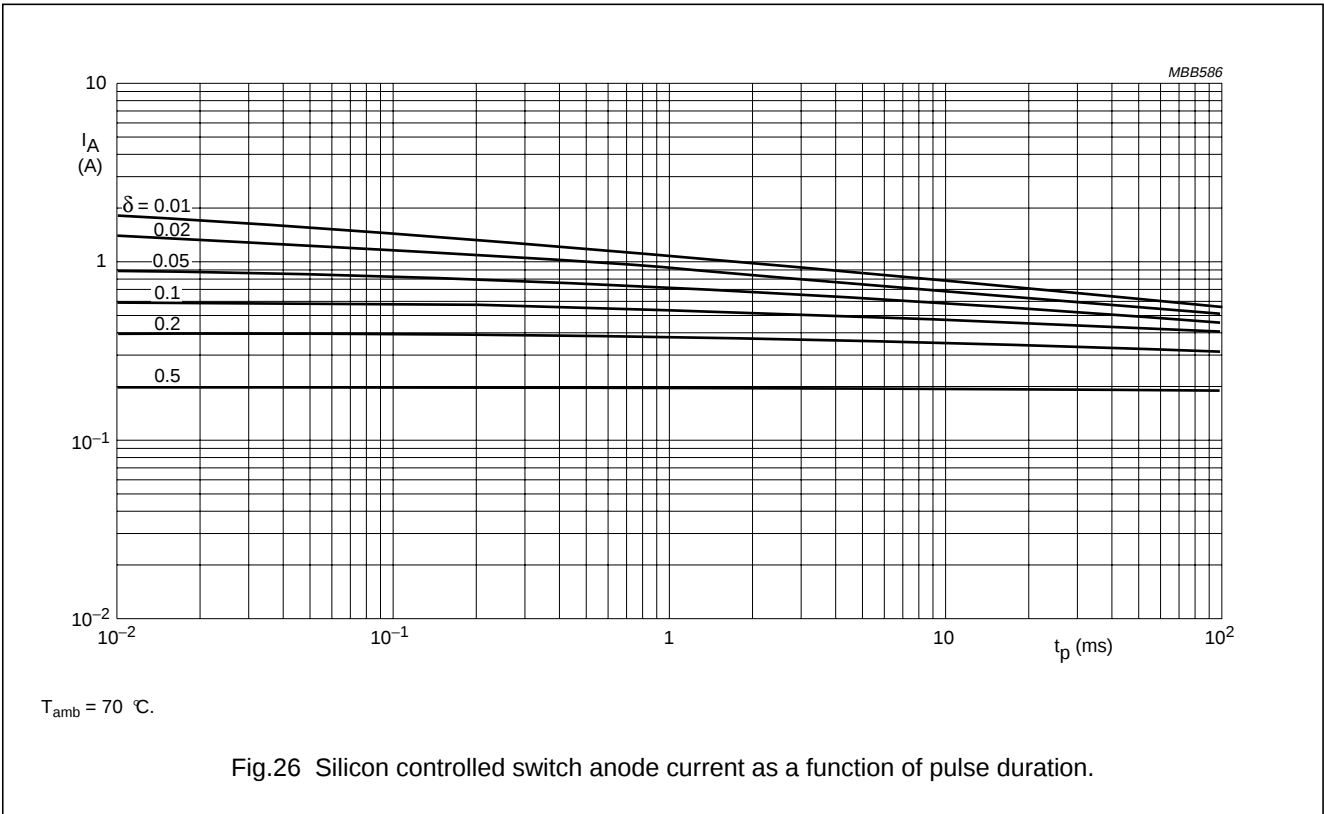
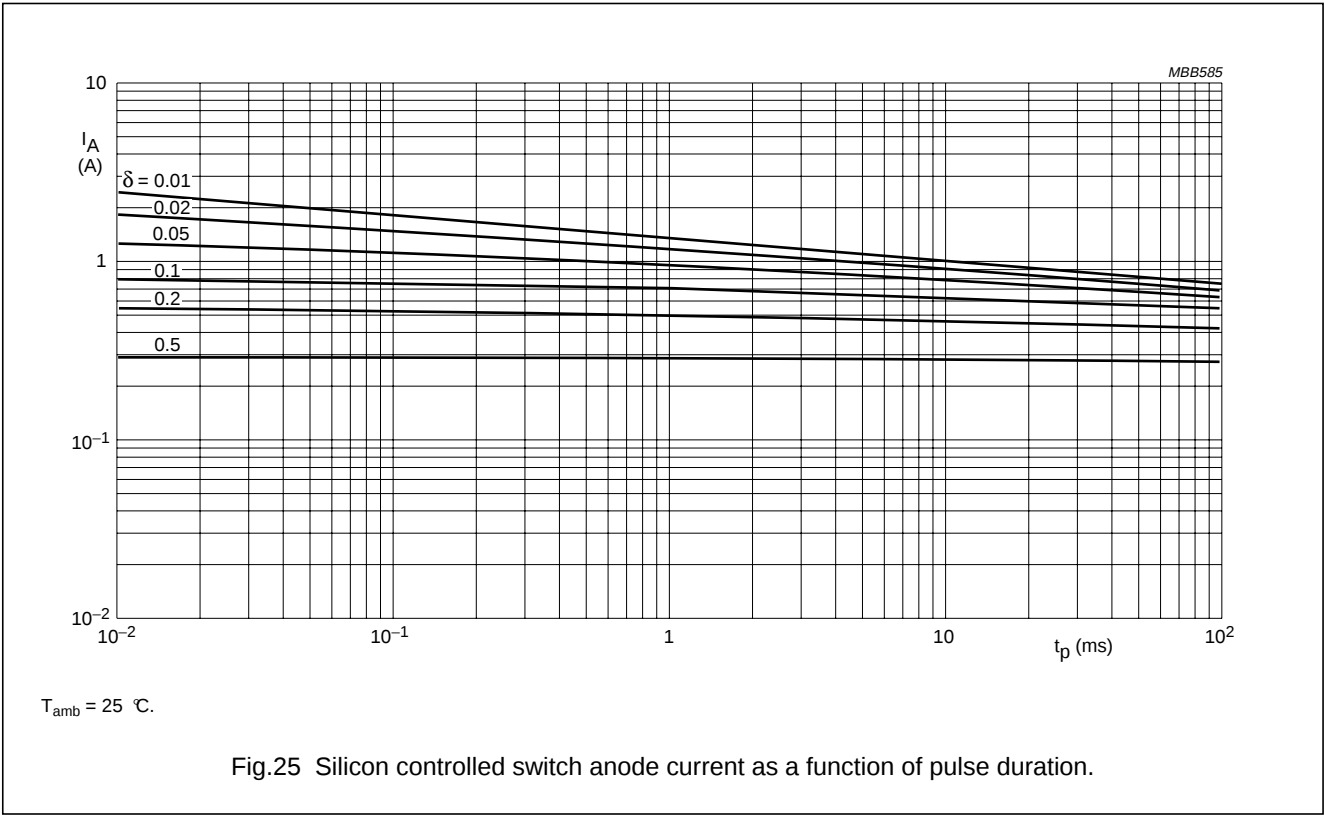
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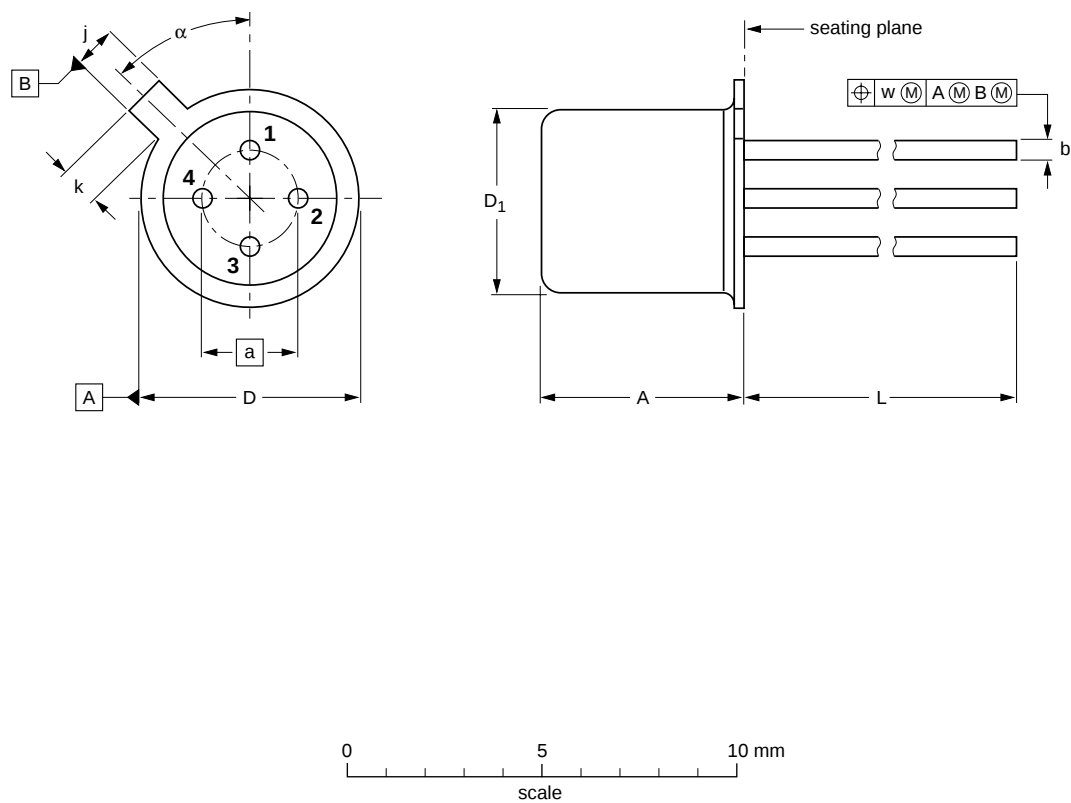
Programmable unijunction transistor/
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BRY39

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 4 leads

SOT18/9



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	5.31 4.74	2.54	0.46 0.42	5.45 5.30	4.70 4.55	1.05 0.95	1.0 0.9	14.5 13.5	0.36	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT18/9	B12/C7 type 3	TO-72				97-04-18

**Programmable unijunction transistor/
Silicon controlled switch**

BRY39**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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